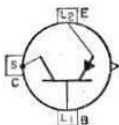


POWER TRANSISTOR



Germanium p-n-p type used in a wide variety of switching and amplifier applications in industrial and military equipment requiring transistors having high voltage, current, and dissipation values. It is used in

2N1100

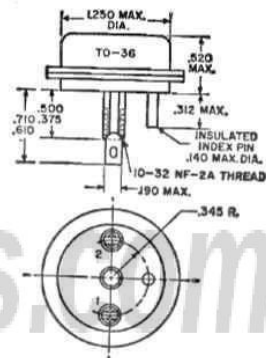
power-switching, voltage- and current-regulating, dc-to-dc converter, inverter, power-supply, and relay- and solenoid-actuating circuits; and in low-frequency oscillator and audio-amplifier service. This type is designed to provide satisfactory performance under extreme environmental conditions of temperature, moisture, and altitude; it is stud-mounted to provide positive heat-sink contact, and has a cold-weld seal to insure reliable performance under severe environmental conditions. JEDEC No. TO-36 package; outline 14, Outlines Section. This type is identical with type 2N174 except for the following items:

MAXIMUM RATINGS

Collector-to-Base Voltage (with emitter-to-base volts = -1.5) ..	-100 max	volts
Emitter-to-Base Voltage (with collector open)	-80 max	volts

CHARACTERISTICS

Collector-to-Emitter Breakdown Voltage (with base short-circuited to emitter and collector amperes = -0.3) ..	-80 min	volts
Emitter-to-Base Voltage (with collector-to-base volts = -100 and emitter current = 0)	-1 max	volt
Collector-to-Emitter Reach-Through Voltage	-100 min	volts
Emitter-Cutoff Current (with emitter-to-base volts = -80 and collector current = 0)	-1	ma
Collector-Cutoff Current (with collector-to-base volts = -100 and emitter current = 0)	-2	ma



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TYPICAL COLLECTOR CHARACTERISTICS

